

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

AC Thyristor Triac power switch in a SOT428 (DPAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	14	A
T _j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 115$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	2	Α





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6		-	-	2	kV
Static char	acteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$		-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$		-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	-	10	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C		850	-	-	V
Dynamic cl	haracteristics		I	I			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 13		500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 2 A; dV_{com}/dt = 10 V/µs; gate open circuit; Fig. 14; Fig. 15		3	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Table 2.	9	IIIIOIIIIatioii		·
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	mb	LD I
2	LD	load		G
3	G	gate		G— CM
mb	LD	mounting base; load	1 3 DPAK (SOT428)	003aaf296

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
ACTT2S-800E	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 115 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	2	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	15.4	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	14	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.98	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 3 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current	t = 20 μs	-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	2	kV

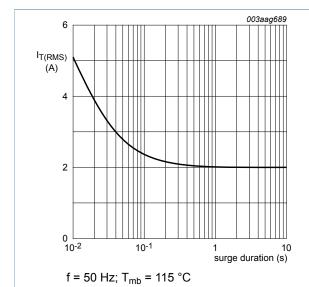


Fig. 1. RMS on-state current as a function of surge duration; maximum values

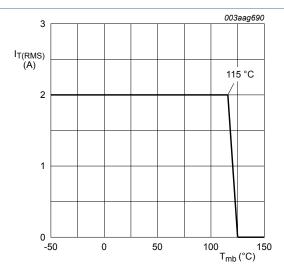


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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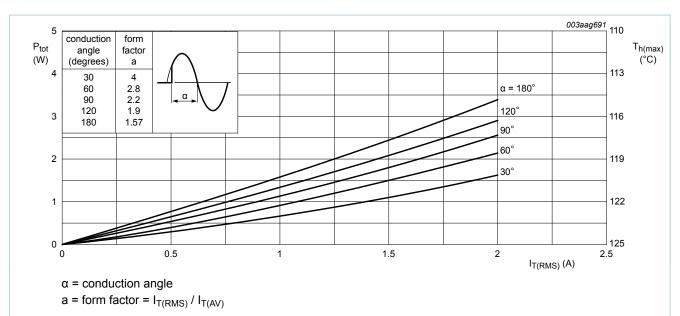


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

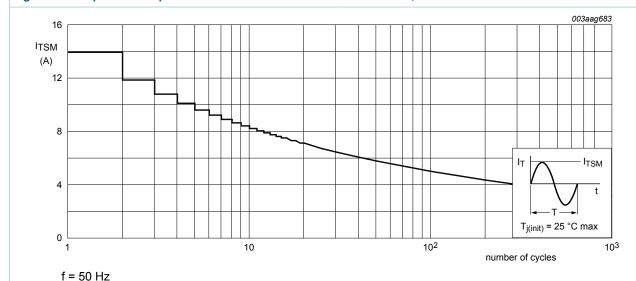


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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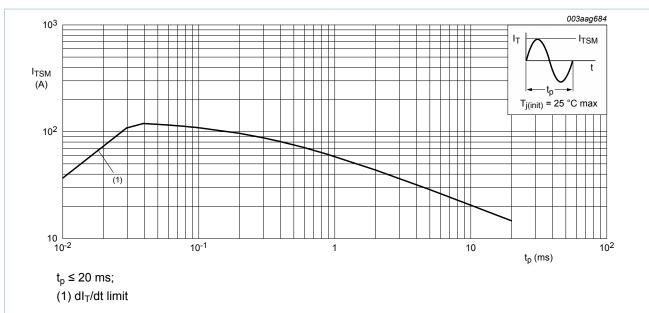


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

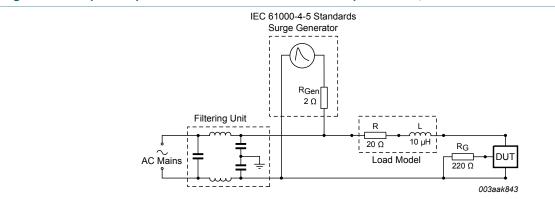


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board (FR4) mounted	-	75	-	K/W

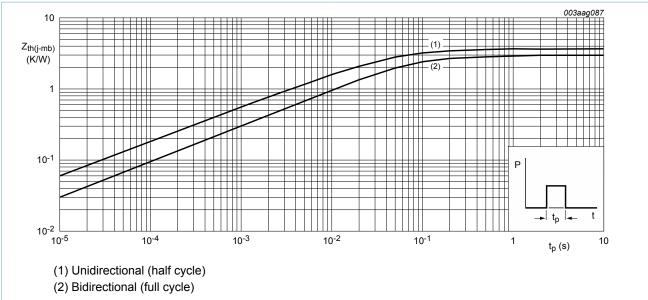


Fig. 7. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	25	mA
		V_D = 12 V; I_G = 100 mA; LD+ G-; T_j = 25 °C; Fig. 9	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	-	-	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	25	mA
V _T	on-state voltage	I _T = 3 A; T _j = 25 °C; <u>Fig. 11</u>	-	-	2	V
V _{GT}	gate trigger voltage	V_D = 12 V; I_T = 100 mA; T_j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 125 °C; Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μA
		V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
V _{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C	850	-	-	V
Dynamic c	haracteristics		· · · · · · · · · · · · · · · · · · ·			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 2 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit};$ Fig. 14; Fig. 15	3	-	-	A/ms

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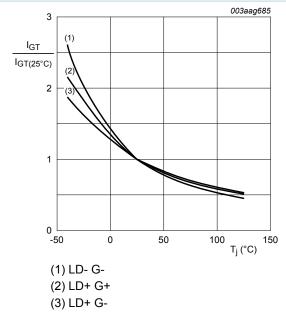


Fig. 8. Normalized gate trigger current as a function of junction temperature

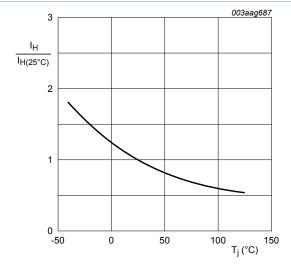


Fig. 10. Normalized holding current as a function of junction temperature

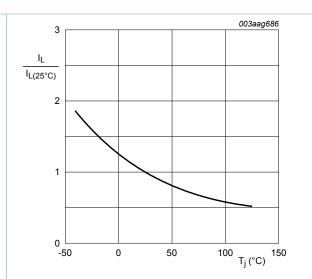
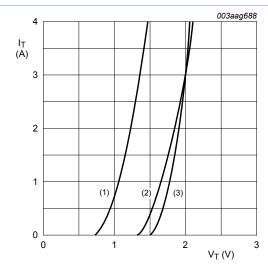


Fig. 9. Normalized latching current as a function of junction temperature



 V_0 = 1.612 V; R_s = 0.120 Ω

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

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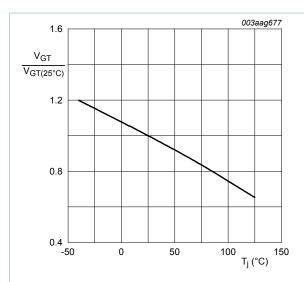
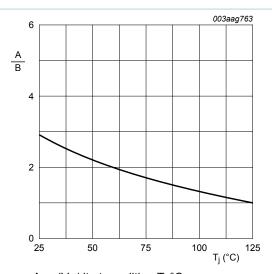
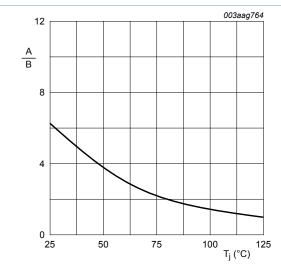


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



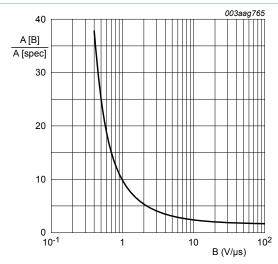
A = dV_D/dt at condition T_j °C B = dV_D/dt at condition T_i [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A = dI_{com}/dt at condition T_j °C B = dI_{com}/dt at condition T_j [125] °C V_D = 400 V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature



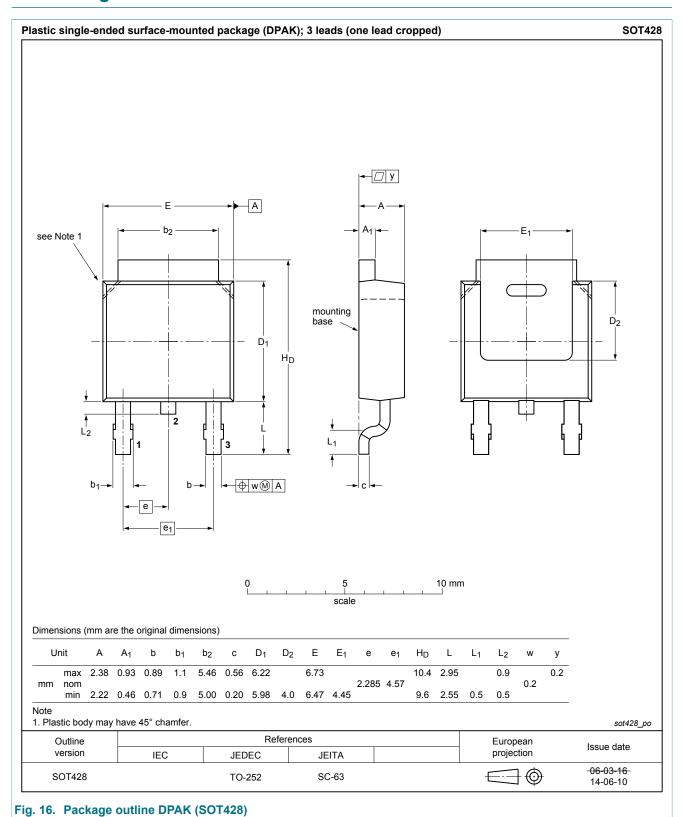
A [B] = dI_{com}/dt at condition B, dV_{com}/dt A [spec] is the data sheet value for dI_{com}/dt turn-off time is less than 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

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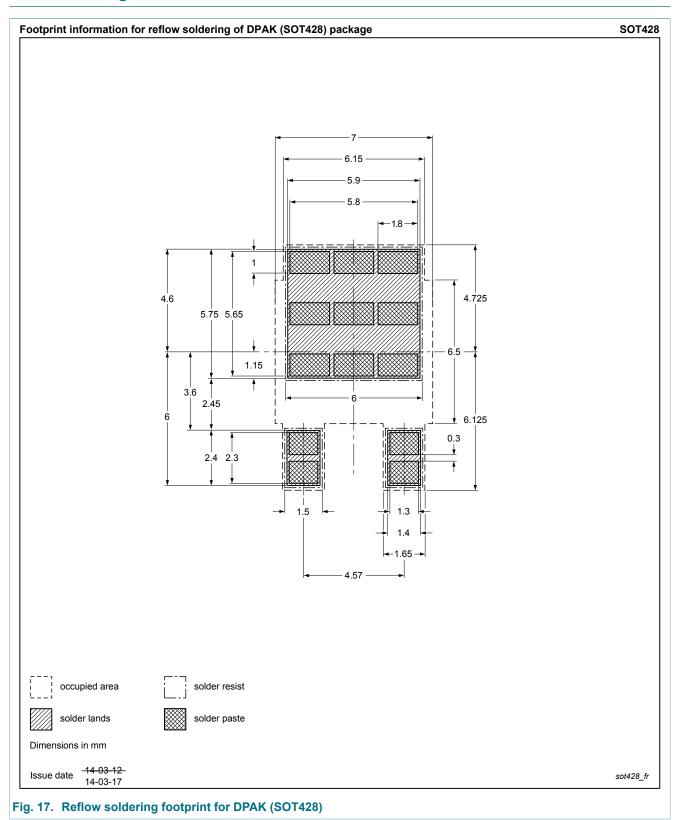
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10. Package outline



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11. Soldering



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